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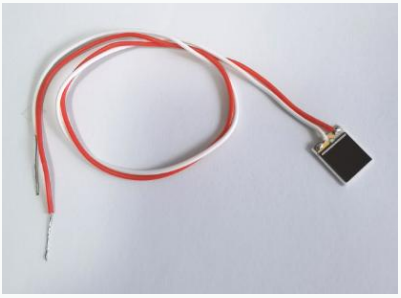
350-1100nm 10mm Si PIN Photodiode

Model:NSP10M



NSP10M

Applications

- Optical power meter
- Optical sensor
- Science analysis
- Industrial automatic control
- Space light detect

Features

- Top illumination Planar PIN PD
- Low dark current, High reliability
- Large active area 10mm×10mm
- The is an un-housed ceramic wafer with an anode and cathode lead wires.

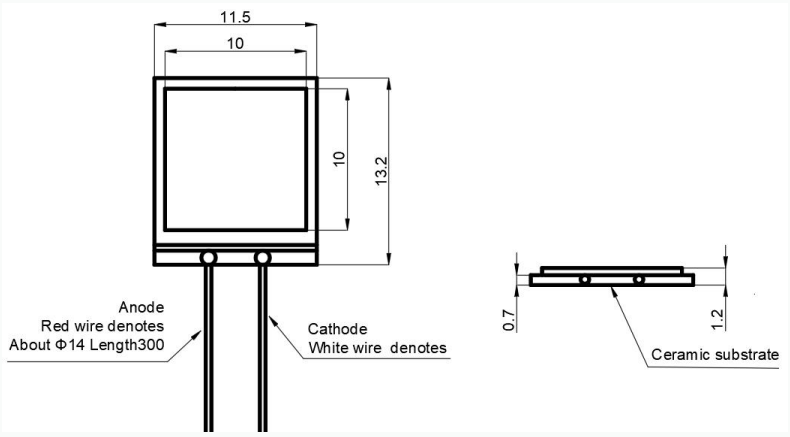
Absolute Maximum Ratings (Tc=25℃)

Parameter	Symbol	Unit	value
Storage temperature	Tst	℃	-40 ~ +85
Operating temperature	Top	℃	-40 ~ +60
Soldering temperature(time)）	Ts（10s）	℃	260
Reverse voltage	Vr	V	20
Forward current	If	mA	18

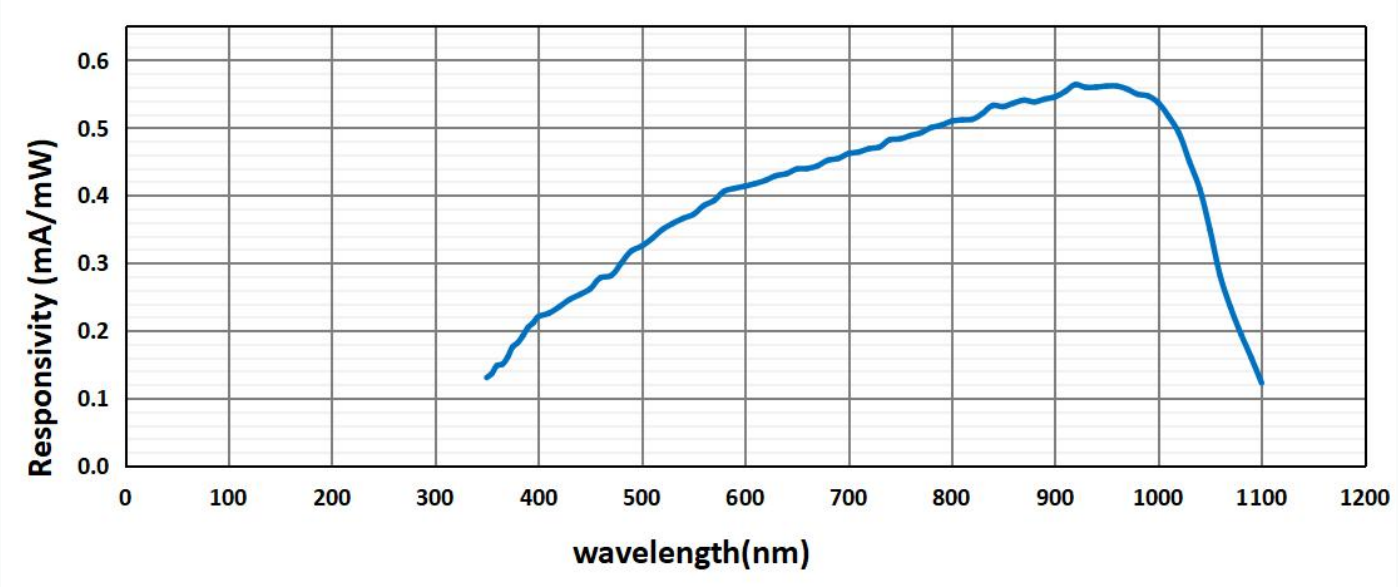
Optical & electrical characteristics (Tc=25℃)

Parameter	Symbol	Test Conditions	Unit	value（Typ.）
Response spectrum	λ		nm	350-1100
Active area			mm	10×10
Responsivity	Re	Vr=5V,λ=350nm	mA/mW	0.1
		Vr=5V,λ=405nm	mA/mW	0.2
		Vr=5V,λ=650nm	mA/mW	0.4
		Vr=5V,λ=850nm	mA/mW	0.5
		Vr=5V,λ=980nm	mA/mW	0.55
Dark current	Id	Vr=0V	nA	0.1
		Vr=5V	nA	1.5
response time	Tr	RL =50Ω,Vr=5V	ns	400
Capacitance	Ct	f=1MHz, Vr=0V	pF	1500
		f=1MHz, Vr=5V	pF	300
Reverse operating voltage	Vr		V	0-10
Reverse breakdown voltage	VBR	Id=10uA	V	70
Saturated optical power	Ps	Vr =5V	mW	25
Shunt resistance	Rsh	Vr =10mV	MΩ	60
Package	Ceramic			

Dimensions and Pin Assignment (mm)



Typical responsivity curve(Tc=25℃)



Order Information

NSP10M：N=Ninglight SP=Si PD 10M=10mm×10mm active area

The cautions

1：The above product specifications are subject to change without notice.

2：The suitable ESD protection is required in storage, transportation and using.